

描述 / Descriptions

TO-251 塑封封装 PNP 半导体三极管。Silicon PNP transistor in a TO-251 Plastic Package.

特征 / Features

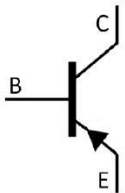
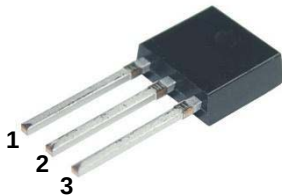
耐压高,饱和压降低,集电极输出电容低,与 MPSA42I(BR3CG42I)互补。

High voltage, Low saturation voltage, low collector capacitance output, complementary pair with MPSA42I(BR3CG42I).

用途 / Applications

高电压控制电路。

High voltage control circuit.

内部等效电路 / Equivalent Circuit**引脚排列 / Pinning**

PIN1 : Base PIN 2 : Collector PIN 3 : Emitter

放大及印章代码 / h_{FE} Classifications & Marking

见印章说明。See Marking Instructions.

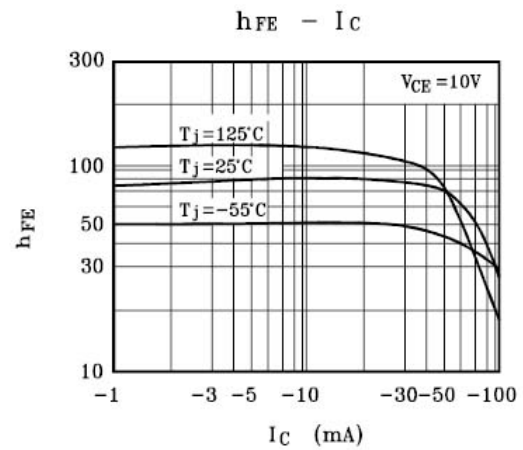
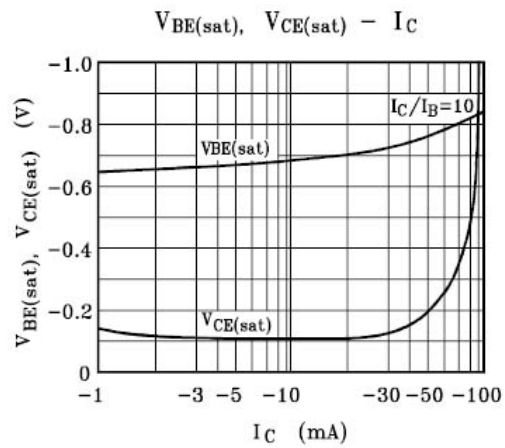
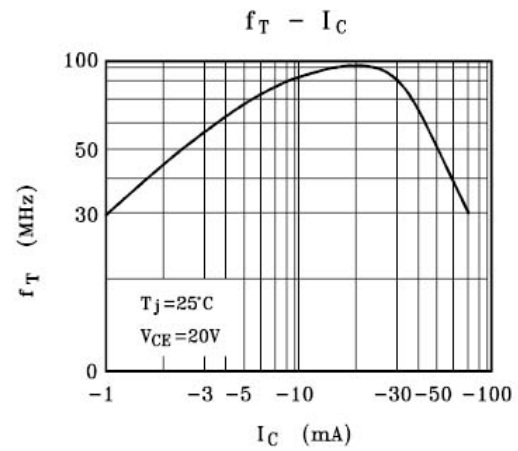
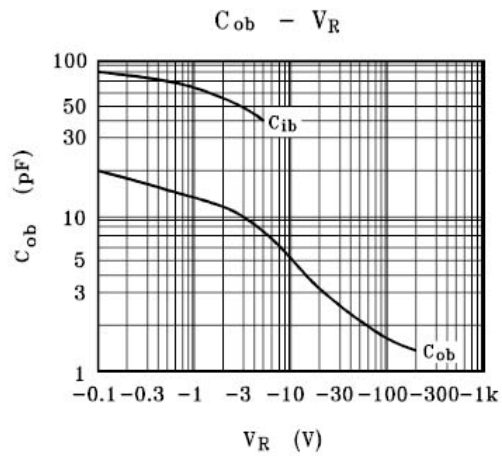
极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Collector to Base Voltage	V_{CBO}	-300	V
Collector to Emitter Voltage	V_{CEO}	-300	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-500	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C

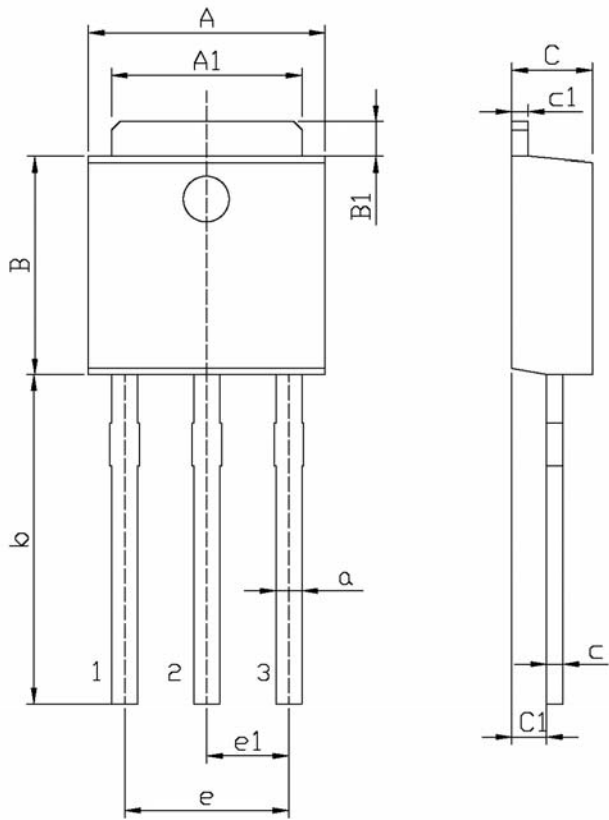
电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C = -100\mu A$ $I_E = 0$	-300			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C = -1.0mA$ $I_B = 0$	-300			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E = -100\mu A$ $I_C = 0$	-5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB} = -200V$ $I_E = 0$			-0.25	μA
Emitter Cut-Off Current	I_{EBO}	$V_{BE} = -3.0V$ $I_C = 0$			-0.1	μA
DC Current Gain ₍₁₎	$h_{FE(1)}$	$V_{CE} = -10V$ $I_C = -10mA$	40			
DC Current Gain ₍₂₎	$h_{FE(2)}$	$V_{CE} = -10V$ $I_C = -30mA$	25			
DC Current Gain ₍₃₎	$h_{FE(3)}$	$V_{CE} = -10V$ $I_C = -1.0mA$	25			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -20mA$ $I_B = -2.0mA$			-0.5	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -20mA$ $I_B = -2.0mA$			-0.9	V
Transition Frequency	f_T	$V_{CE} = -20V$ $f = 100MHz$ $I_C = -10mA$	50			MHz
Collector output capacitance	C_{cb}	$V_{CB} = -20V$ $f = 1.0MHz$ $I_E = 0$			6.0	pF

电参数曲线图 / Electrical Characteristic Curve



外形尺寸图 / Package Dimensions

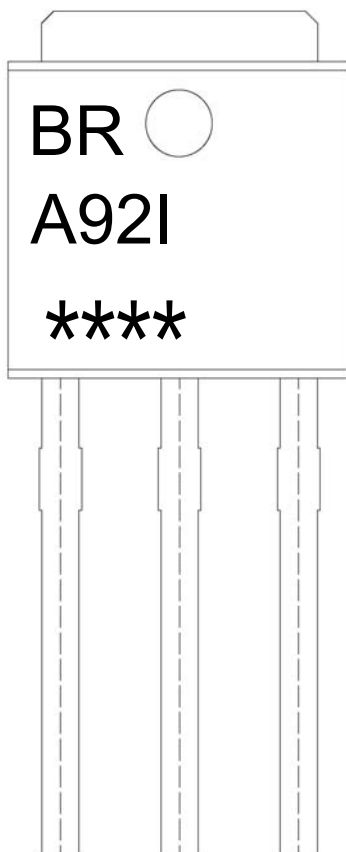


单位：mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	6.45	6.75	a	0.64	0.74
A1	5.20	5.40	b	9.00	9.40
B	5.95	6.25	c	0.45	0.55
B1	0.95	1.25	c1	0.45	0.55
C	2.20	2.40	e1	2.24	2.34
C1	0.95	1.15	e	4.43	4.73

TO-251

印章说明 / Marking Instructions



说明：

BR： 为公司代码

A92I： 为型号代码

****： 为生产批号代码，随生产批号变化。

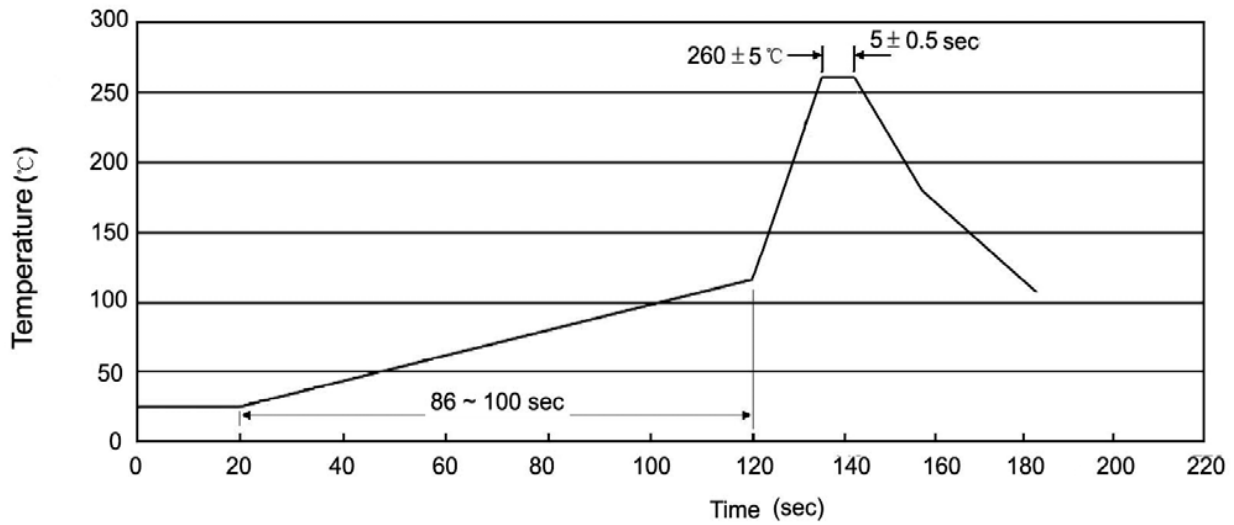
Note:

BR: Company Code

A92I: Product Type.

****: Lot No. Code, code change with Lot No.

波峰焊温度曲线图(无铅) / Temperature Profile for Dip Soldering(Pb-Free)



说明：

- 1、预热温度 25~150°C，时间 60~90sec;
- 2、峰值温度 260±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2~10°C/sec.

Note:

- 1.Preheating:25~150°C, Time:60~90sec.
- 2.Peak Temp.:260±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：270±5°C

时间：10±1 sec.

Temp.:270±5°C

Time:10±1 sec

包装规格 / Packaging SPEC.

散件包装 / BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Bag 只/袋	Bags/Inner Box 袋/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Bag 袋	Inner Box 盒	Outer Box 箱
TO-251	1,000	10	10,000	5	50,000	135×190	237×172×102	560×245×195

套管包装 / TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱
TO-251/252	75	48	3,600	5	18,000	526×20.5×5.25	555×164×50	575×290×180

使用说明 / Notices